2014 International Workshop on EUV Lithography

June 23-27, 2014

Makena Beach & Golf Resort • Maui, Hawaii

Workshop Agenda

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Workshop Agenda Outline

Monday, June 23, 2014

8:30 AM -5:00 PM

EUV Lithography Short Course

Tuesday, June 24, 2014

3:00 PM - 5:00 PM

Registration (Kaeo Ballroom Foyer) Speaker Prep (Wailea Salon)

6:00 PM - 7:30 PM

Reception (Pacific Lawn)

Wednesday, June 25, 2014

| 7:30 AM – 8:30 AM | Breakfast (Café Kiowai) |
|---------------------|-----------------------------------|
| 8:30 AM - 11:40 AM | Oral Presentations (Wailea Salon) |
| 11:40 AM - 12:40 PM | 1 Lunch (Molokini Room) |
| 12:25 PM - 3:30 PM | Oral Presentations (Wailea Salon) |
| 3:30 PM A | fternoon off for Networking |



Thursday, June 26, 2014

- 7:30 AM 8:30 AM Breakfast (Café Kiowai)
- 8:30 AM 12:00 PM Oral Presentations (Wailea Salon)
- 11:30 PM 12:30 PM Lunch (Molokini Room)
- 12:30 PM 4:05 PM Oral Presentations (Wailea Salon)
- 4:30 PM 5:30 PM Poster Session
- 6:30 PM 8:00 PM Dinner (Pacific Lawn)

Friday, June 27, 2014

8:30 AM – 10:00 AM EUVL Workshop Steering Committee Meeting (Kaeo Ballroom)



2014 International Workshop on EUV Lithography

Makena Beach & Golf Resort, Maui, Hawaii, USA June 23-27, 2014

<u>Workshop Agenda</u>

Monday, June 23, 2014

Short Courses

EUV Lithography by Vivek Bakshi (EUV Litho, Inc.), Patrick Naulleau (LBNL) and Jinho Ahn (Hanyang University)

8:30 AM -5:00 PM

<u> Tuesday, June 24, 2014</u>

Registration and Reception

- 3:00 PM- 5:00 PM Registration & Speaker Prep
- 6:00 PM- 7:30 PM Reception



Wednesday, June 25, 2014

8:30 AM Welcome and Introduction

Introductions (Intro-1) Vivek Bakshi EUV Litho, Inc., Austin, TX, USA

Session 1: Keynote – 1

EUV: The Computational Landscape (P1)

Vivek Singh Intel Corporation, MS: RA3-254, 2501 N.W. 229th Ave, Hillsboro, OR 97124

One hundred Watt Operation Demonstration of HVM LPP-EUV Source (P2)

<u>Hakaru Mizoguchi</u>, Hiroaki Nakarai, Tamotsu Abe, Takeshi Ohta, Krzysztof M Nowak, Yasufumi Kawasuji, Hiroshi Tanaka, Yukio Watanabe, Tsukasa Hori, Takeshi Kodama, Yutaka Shiraishi, Tatsuya Yanagida, Georg Soumagne, Tsuyoshi Yamada, Taku Yamazaki, Shinji Okazaki and Takashi Saitou

Gigaphoton Inc. Hiratsuka facility: 3-25-1 Shinomiya Hiratsuka Kanagawa, 254-8567, JAPAN

Break

Session 2: EUV Sources

Development of Scalable Laser Technology for EUVL applications (Invited Talk) (P21)

<u>Tomas Mocek</u>, Akira Endo, Taisuke Miura *HiLASE Project, Institute of Physics ASCR, Prague, Czech Republic*

Gain Enhancements of CO₂ Laser Amplifiers by Using Transverse-gas-flow Configuration to Boost up Driving Powers for EUV Generation (Invited Talk) (P24)

<u>Koji Yasui</u>¹ and Jun-ichi Nishimae² ¹*Mitsubishi Electric Corporation, Head quarter, Tokyo, Japan* ²*Mitsubishi Electric Corporation, Advanced technology R&D center, Hyogo, Japan*



Colliding Laser-Produced Plasmas as Targets for Laser-Generated EUV Sources (P25)

T. Cummins¹, C. O'Gorman¹, <u>P. Dunne¹</u>, E. Sokell¹, G. O'Sullivan¹ and P. Hayden^{1,2}.
1)School of Physics, University College Dublin, Belfield, Dublin 4, Ireland.
2)National Centre for Plasma Science and Technology, Dublin City University, Glasnevin, Dublin 9, Ireland

In-Situ Cleaning of Sn EUV Sources (Invited Talk) (P42)

<u>David N. Ruzic</u>, Daniel Elg, Ivan Shchelkanov Center for Plasma-Material Interactions; Department of Nuclear, Plasma and Radiological Engineering, University of Illinois at Urbana-Champaign, Illinois, USA

EUV Source: Progress & Challenges (Invited Talk) (P27)

<u>Klaus Schuegraf</u> et al *Cymer, San Diego, CA, USA*

12:00 PM - 1:00 PM

Lunch

Session 3: Regional Reviews

Korea (Jinho Ahn) Japan (Hiroo Kinoshita) Taiwan (TBD) China (Yanqui Li) USA (Greg Denbeaux) Europe (Padraig Dunne)

Break

Session 4: EUV Optics

Progress of Optical Design for EUV Lithography tools in BIT (Invited talk) (P56)

<u>Yanqiu Li</u>, Fei Liu, Qiuli Mei, Zhen Cao, Yan Liu Key Laboratory of Photoelectron Imaging Technology and System (Ministry of Education of China), School of Optoelectronics, Beijing Institute of Technology, Beijing 10081, P.R. China

CNC Fabrication of High NA Aspheric Optics for EUVL Applications (P53)

Phil Baker, Richard Pultar, Dr. Riley Aumiller



Error Compensation Phase Extraction Algorithm Used in Phase Shifting Point Diffraction Interferometer (P52)

Jie Yu, Haitao Zhang, Dongmei Ma, Chunshui Jin State Key Laboratory of Applied Optics, Changchun Institute of Optics, Fine Mechanics & Physics, Chinese Academy of Sciences, No. 3888, Dongnanhu Road, Changchun, Jilin, People's Republic of China

Large Reflectometer for EUV Optics (P55)

Hiroo Kinoshita^{1,2}, Tetsuo Harada^{1,2}, Takeo Watanabe^{1,2} ¹⁾ Center for EUV Lithography, University of Hyogo, Kamigori, Hyogo 678-1205, Japan ²⁾ JST, CREST, Kawaguchi, Saitama 331-0012, Japan

Progress with EUV optics deposition at RIT (Invited Talk) (P56)

Yuriy Platonov, Michael Kriese, Vladimir Martynov, Raymond Crucet, Yang Li, Jim Rodriguez, Licai Jiang, Gary Fournier, Jerry Hummel *Rigaku Innovative Technologies, 1900 Taylor Rd., Auburn Hills, MI 48326, USA*

Adjourn: Time off for Networking

End Day 1



Day 2: Thursday, June 26, 2014

Welcome and Announcements (Intro-2) Vivek Bakshi EUV Litho, Inc.

Session 5: Keynote-2

Current status and expectation of EUV lithography (P3)

Takayuki UCHIYAMA Lithography Process Development Department, Center for Semiconductor Research and Development, TOSHIBA Corporation

Break

Session 6: EUV Masks

A New EUV Mask Blank Defect Inspection Method with Coherent Diffraction Imaging (Invited Talk) (P63)

Ding Qi^a, <u>Kuen-Yu Tsai</u>^a and Jia-han Li^b ^a Department of Electrical Engineering, National Taiwan University, Taipei 106, Taiwan ^b Department of Engineering Science and Ocean Engineering, National Taiwan University, Taipei 106, Taiwan

Recent Results from the Measurement of Reflectivity of EUV Lithography Masks Blanks and Absorbers (Invited Talk) (P64)

Rupert C. C. Perera EUV Tech, 2840 Howe Road Suite A, Martinez, CA 94553, USA

Improved Stochastic Imaging Properties in Contact Hole Pattern by Using Attenuated PSM for EUVL (P65)

Jung Sik Kim¹, Seongchul Hong², Jae Uk Lee², Seung Min Lee², Jung Hwan Kim², Hyun Min Song¹, and Jinho Ahn^{1,2} ¹Department of Nanoscale Semiconductor Engineering ²Department of Materials Science and Engineering Hanyang University, 222 Wangsimni-ro, Seongdong-gu, Seoul 133-791, Korea

Advanced Mask Patterning: Inspection/Metrology and Cleans Requirements & Approaches (P68)

Sushil Padiyar et al AMAT



Overview of Actinic Mask Inspection System in NewSUBARU (Invited Talk) (P67)

Hiroo Kinoshita^{1,3}, Tetsuo Harada^{1,3}, Yutaka Nagata^{2,3}, Takeo Watanabe^{1,3} and Katsumi Midorikawa²

- ¹⁾ Center for EUV Lithography, University of Hyogo, Kamigori, Hyogo 678-1205, Japan
- ²⁾ Riken ASI, Wako, Saitama 351-0198, Japan
- ³⁾ JST, CREST, Kawaguchi, Saitama 331-0012, Japan

Lunch

Session 7: EUV Resists

Theoretical Study on Stochastic Effects in Chemically Amplified Resist Process for Extreme Ultraviolet Lithography (Invited Talk) (P71)

Takahiro Kozawa¹, Julius Joseph Santillan², and Toshiro Itani² ¹The Institute of Scientific and Industrial Research, Osaka University, 8-1 Mihogaoka, Ibaraki, Osaka 567-0047, Japan ²EUVL Infrastructure Development Center, Inc. (EIDEC)

Direct Visualization of the Impacts of EUV Mask Roughness (Invited Talk) (P72)

Patrick Naulleau LBNL, Berkeley, CA, USA

Novel EUV Resist Materials and EUV Resist Defects (Invited Talk) (P74)

Yoshi Hishiro JSR Micro INC, 1280 N. Mathilda Ave, Sunnyvale, CA 94089, USA

The Role of Secondary Electrons in EUV Resist (Invited Talk) (P75)

Greg Denbeaux et al University of Albany, Albany, NY, USA

Optics Contamination from Resist Outgassing: Lessons Learned (Invited Talk) (P41)

<u>C. Tarrio</u>, S. B. Hill, R. F. Berg, S. Grantham, and T. B. Lucatorto National Institute of Standards and Technology, Gaithersburg, MD, USA

Additional Paper(s) in the EUV Resist session to be announced.

Break



Session 8: Panel Discussion

Topic: Can EUVL deliver patterning solutions for 7nm node?

Moderators

Sushil Padiyar Applied Materials

Vivek Bakshi EUV Litho, Inc.

Panelists

Vivek Singh Intel

Hakaru Mizoguchi Gigaphoton

Takayuki UCHIYAMA *Toshiba*

EUVL Workshop Summary (P90)

Vivek Bakshi EUV Litho, Inc.

Break

4:30- 5:30 PM Poster Session



Session 9: Poster Session

Modulation of the Langmuir Oscillation on the plasma radiation by Rabi oscillation (P22)

Xiangdong Li State Key Laboratory of High Field Laser Physics, Shanghai Institute of Optics and Fine Mechanics, Shanghai (201800), People's Republic of China

EUV Radiation Characteristics of Xe Cluster Ensemble Irradiated by Nanosecond and Femtosecond Lasers (P23)

<u>Cheng Wang</u>, Zongxin Zhang, Guande Wang, Yuxin Leng, Quanzhong Zhao, Ruxin Li State Key Laboratory of High Field Laser Physics, Shanghai Institute of Optics and Fine Mechanics, Chinese Academy of Sciences (CAS), Shanghai 201800, China

The Energetiq EQ-10 EUV Source for Metrology (P26)

Stephen F. Horne, Matthew J. Partlow, <u>Deborah S. Gustafson</u>, Matthew M. Besen, Donald K. Smith, Paul A. Blackborow Energetig Technology Inc., 7 Constitution Way, Woburn MA 01801 USA

A Novel Model for Coated System Analysis in Extreme Ultra-Violet Lithography (P51)

Wang Jun

State Key Laboratory of Applied Optics, Changchun Institute of Optics, Fine Mechanics and Physics, Chinese Academy of Sciences, 3888# Dong Nanhu Road, Changchun, Jilin, 130033, China

Comparison of High Precision Profilometry to Lateral Shearing Interferometry Collected from High NA Aspheric Surfaces with Materials from SIC, Aluminum, ULE and Zerodur (P54)

<u>Richard Pultar</u>, Phil Baker, Dr. Riley Aumiller HNu Photonics, LLC, 350 Hoohana St, Kahului HI 96732, USA

Simplified Model for Spectrum Simulation of Multilayer with Buried Defect in EUV Lithography (P61)

<u>Xiangzhao Wang</u>, Sikun Li, Xiaolei Liu Laboratory of Information Optics and Opt-Electronic Technology, Shanghai Institute of Optics and Fine Mechanics, Chinese Academy of Sciences, Shanghai 201800, China</u>



Measurement of Deflection of the Full scale Free Standing EUV Pellicle (P62)

Eun-Sang Park, Zahid Hussain Shamsi, Ji-Won Kim, Dai-Gyoung Kim, and Hye-Keun Oh Hanyang University, 222 Wangsimni-ro, Seongdong-gu, Seoul 133-791, Korea



Friday, June 27, 2014

8:30 AM - 10:00 AM

EUVL Workshop Steering Committee Meeting (Kaeo Ballroom)

- 8:30 AM 9:00 AM Breakfast
- 9:00 AM 10:00 AM Steering Committee Meeting



